

# Mantu Hudait

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

109  
papers

2,680  
citations

28  
h-index

47  
g-index

124  
ext. papers

2,993  
ext. citations

3.8  
avg, IF

4.98  
L-index

#	Paper	IF	Citations
109	Mapping the Interfacial Electronic Structure of Strain-Engineered Epitaxial Germanium Grown on In Al As Stressors.. <i>ACS Omega</i> , <b>2022</b> , 7, 5946-5953	3.9	0
108	Design, Theoretical, and Experimental Investigation of Tensile-Strained Germanium Quantum-Well Laser Structure. <i>ACS Applied Electronic Materials</i> , <b>2021</b> , 3, 4535-4547	4	2
107	Device Characterization of a Sulfur-Implanted p <sup>++</sup> /p GaSb Photovoltaic Camel Diode. <i>IEEE Journal of Photovoltaics</i> , <b>2020</b> , 10, 1675-1680	3.7	1
106	Tri-gate GaN junction HEMT. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 143506	3.4	12
105	Magnetic Damping in Epitaxial Iron Alloyed with Vanadium and Aluminum. <i>Physical Review Applied</i> , <b>2020</b> , 14,	4.3	6
104	Structural, morphological and magnetotransport properties of composite semiconducting and semimetallic InAs/GaSb superlattice structure. <i>Materials Advances</i> , <b>2020</b> , 1, 1099-1112	3.3	1
103	Electronic and optical properties of highly boron-doped epitaxial Ge/AlAs(001) heterostructures. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 075702	2.5	0
102	Engineering the Interfacial Electronic Structure of Epitaxial Ge/AlAs(001) Heterointerfaces via Substitutional Boron Incorporation: The Roles of Doping and Interface Stoichiometry. <i>ACS Applied Electronic Materials</i> , <b>2019</b> , 1, 2646-2654	4	2
101	TBAL: Tunnel FET-Based Adiabatic Logic for Energy-Efficient, Ultra-Low Voltage IoT Applications. <i>IEEE Journal of the Electron Devices Society</i> , <b>2019</b> , 7, 210-218	2.3	10
100	Magnetic Field Sensing by Exploiting Giant Nonstrain-Mediated Magnetodielectric Response in Epitaxial Composites. <i>Nano Letters</i> , <b>2018</b> , 18, 2835-2843	11.5	10
99	Metal work function engineering on epitaxial (100)Ge and (110)Ge metal-oxide-semiconductor devices. <i>Microelectronic Engineering</i> , <b>2018</b> , 199, 80-86	2.5	3
98	Nonlinear DC equivalent circuits for ferroelectric memristor and Its FSM application. <i>Integrated Ferroelectrics</i> , <b>2018</b> , 192, 16-27	0.8	3
97	In Situ SiO Passivation of Epitaxial (100) and (110)InGaAs by Exploiting TaSiO Atomic Layer Deposition Process. <i>ACS Omega</i> , <b>2018</b> , 3, 14567-14574	3.9	2
96	Heterogeneous integration of InAs/GaSb tunnel diode structure on silicon using 200 nm GaAsSb dislocation filtering buffer. <i>AIP Advances</i> , <b>2018</b> , 8, 105108	1.5	1
95	Structural and optical properties of sulfur passivated epitaxial step-graded GaAs <sub>1-y</sub> Sb <sub>y</sub> materials. <i>AIP Advances</i> , <b>2018</b> , 8, 115119	1.5	2
94	Direct and indirect band gaps in Ge under biaxial tensile strain investigated by photoluminescence and photoreflectance studies. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	9
93	An Energy-Efficient Tensile-Strained Ge/InGaAs TFET 7T SRAM Cell Architecture for Ultralow-Voltage Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 2193-2200	2.9	22

92	Investigating FinFET Sidewall Passivation Using Epitaxial (100)Ge and (110)Ge MetalOxideSemiconductor Devices on AlAs/GaAs. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 4457-4465	2.9	3
91	Growth, structural, and electrical properties of germanium-on-silicon heterostructure by molecular beam epitaxy. <i>AIP Advances</i> , <b>2017</b> , 7, 095214	1.5	13
90	The permittivity and refractive index measurements of doped barium titanate (BT-BCN). <i>Optical Materials</i> , <b>2017</b> , 73, 793-798	3.3	7
89	Band Offset Enhancement of a-Al <sub>2</sub> O <sub>3</sub> /Tensile-Ge for High Mobility Nanoscale pMOS Devices. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1196-1199	4.4	4
88	Transport Across Heterointerfaces of Amorphous Niobium Oxide and Crystallographically Oriented Epitaxial Germanium. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 43315-43324	9.5	2
87	Performance Analysis of TaSiOx Inspired Sub-10 nm Energy Efficient In <sub>0.53</sub> Ga <sub>0.47</sub> As Quantum Well Tri-Gate Technology. <i>IEEE Journal of the Electron Devices Society</i> , <b>2017</b> , 5, 496-503	2.3	
86	Pushing the limits of silicon transistors <b>2016</b> ,		1
85	Heterogeneously grown tunable group-IV laser on silicon <b>2016</b> ,		2
84	Growth and characterization of metamorphic InAs/GaSb tunnel heterojunction on GaAs by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 244308	2.5	7
83	<b>2016</b> ,		2
82	Integration of lead-free ferroelectric on HfO <sub>2</sub> /Si (100) for high performance non-volatile memory applications. <i>Scientific Reports</i> , <b>2015</b> , 5, 8494	4.9	32
81	Lead-free epitaxial ferroelectric material integration on semiconducting (100) Nb-doped SrTiO <sub>3</sub> for low-power non-volatile memory and efficient ultraviolet ray detection. <i>Scientific Reports</i> , <b>2015</b> , 5, 12415	4.9	34
80	Heteroepitaxial Ge MOS Devices on Si Using Composite AlAs/GaAs Buffer. <i>IEEE Journal of the Electron Devices Society</i> , <b>2015</b> , 3, 341-348	2.3	11
79	Integration of SrTiO <sub>3</sub> on crystallographically oriented epitaxial germanium for low-power device applications. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 5471-9	9.5	20
78	Functionally Graded Interfaces: Role and Origin of Internal Electric Field and Modulated Electrical Response. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 22458-68	9.5	10
77	Magnetotransport Properties of Epitaxial Ge/AlAs Heterostructures Integrated on GaAs and Silicon. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 22315-21	9.5	6
76	Performance Evaluation of Novel Strain-Engineered Ge-InGaAs Heterojunction Tunnel Field-Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 3223-3228	2.9	9
75	Strain-Engineered Biaxial Tensile Epitaxial Germanium for High-Performance Ge/InGaAs Tunnel Field-Effect Transistors. <i>IEEE Journal of the Electron Devices Society</i> , <b>2015</b> , 3, 184-193	2.3	20

74	Tailoring the Valence Band Offset of Al <sub>2</sub> O <sub>3</sub> on Epitaxial GaAs(1-y)Sb(y) with Tunable Antimony Composition. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 28624-31	9.5	16
73	Heterogeneously-Grown Tunable Tensile Strained Germanium on Silicon for Photonic Devices. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 26470-81	9.5	14
72	Mixed-anion GaAs <sub>1-y</sub> Sb <sub>y</sub> graded buffer heterogeneously integrated on Si by molecular beam epitaxy. <i>Applied Physics Express</i> , <b>2015</b> , 8, 025501	2.4	4
71	Heterointerface engineering of broken-gap InAs/GaSb multilayer structures. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2015</b> , 7, 2512-7	9.5	17
70	Reliability Studies on High-Temperature Operation of Mixed As/Sb Staggered Gap Tunnel FET Material and Devices. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2014</b> , 14, 245-254	1.6	25
69	Tensile-strained nanoscale Ge/In <sub>0.16</sub> Ga <sub>0.84</sub> As heterostructure for tunnel field-effect transistor. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 4947-53	9.5	7
68	Reduced erbium-doped ceria nanoparticles: one nano-host applicable for simultaneous optical down- and up-conversions. <i>Nanoscale Research Letters</i> , <b>2014</b> , 9, 231	5	29
67	Heterogeneous integration of epitaxial Ge on Si using AlAs/GaAs buffer architecture: suitability for low-power fin field-effect transistors. <i>Scientific Reports</i> , <b>2014</b> , 4, 6964	4.9	22
66	Design and Modeling of Metamorphic Dual-Junction InGaP/GaAs Solar Cells on Si Substrate for Concentrated Photovoltaic Application. <i>IEEE Journal of Photovoltaics</i> , <b>2014</b> , 4, 1683-1689	3.7	7
65	Germanium Based Field-Effect Transistors: Challenges and Opportunities. <i>Materials</i> , <b>2014</b> , 7, 2301-2339	3.5	96
64	Growth, strain relaxation properties and high- $\epsilon$ dielectric integration of mixed-anion GaAs <sub>1-y</sub> Sb <sub>y</sub> metamorphic materials. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 134304	2.5	4
63	III-V Multijunction Solar Cell Integration with Silicon: Present Status, Challenges and Future Outlook. <i>Energy Harvesting and Systems</i> , <b>2014</b> , 1,	4.4	41
62	Interfacial band alignment and structural properties of nanoscale TiO <sub>2</sub> thin films for integration with epitaxial crystallographic oriented germanium. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 024303	2.5	11
61	X-ray photoelectron spectroscopy analysis and band offset determination of CeO <sub>2</sub> deposited on epitaxial (100), (110), and (111)Ge. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 011217	1.3	33
60	Design, fabrication, and analysis of p-channel arsenide/antimonide hetero-junction tunnel transistors. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 044502	2.5	17
59	Quasi-zero lattice mismatch and band alignment of BaTiO <sub>3</sub> on epitaxial (110)Ge. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 024303	2.5	7
58	Structural and band alignment properties of Al <sub>2</sub> O <sub>3</sub> on epitaxial Ge grown on (100), (110), and (111)GaAs substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 134311	2.5	28
57	Ultra-high frequency photoconductivity decay in GaAs/Ge/GaAs double heterostructure grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 093119	3.4	0

56	Energy band alignment of atomic layer deposited HfO <sub>2</sub> on epitaxial (110)Ge grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 093109	3.4	11
55	BaTiO <sub>3</sub> integration with nanostructured epitaxial (100), (110), and (111) germanium for multifunctional devices. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 11446-52	9.5	10
54	Impact of Threading Dislocations on the Design of GaAs and InGaP/GaAs Solar Cells on Si Using Finite Element Analysis. <i>IEEE Journal of Photovoltaics</i> , <b>2013</b> , 3, 528-534	3.7	26
53	Low-power tunnel field effect transistors using mixed As and Sb based heterostructures. <i>Nanotechnology Reviews</i> , <b>2013</b> , 2, 637-678	6.3	28
52	Energy band alignment of atomic layer deposited HfO <sub>2</sub> oxide film on epitaxial (100)Ge, (110)Ge, and (111)Ge layers. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 114303	2.5	18
51	Band offset determination of mixed As/Sb type-II staggered gap heterostructure for n-channel tunnel field effect transistor application. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 024319	2.5	17
50	Structural, morphological, and defect properties of metamorphic In <sub>0.7</sub> Ga <sub>0.3</sub> As/GaAs <sub>0.35</sub> Sb <sub>0.65</sub> p-type tunnel field effect transistor structure grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2013</b> , 31, 041203	1.3	9
49	Structural, morphological, and band alignment properties of GaAs/Ge/GaAs heterostructures on (100), (110), and (111) GaAs substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2013</b> , 31, 011206	1.3	28
48	CV characteristics of epitaxial germanium metaloxide semiconductor capacitor on GaAs substrate with ALD Al <sub>2</sub> O <sub>3</sub> dielectric. <i>Microelectronic Engineering</i> , <b>2012</b> , 97, 16-19	2.5	4
47	In situ grown Ge in an arsenic-free environment for GaAs/Ge/GaAs heterostructures on off-oriented (100) GaAs substrates using molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 051205	1.3	18
46	Barrier-Engineered Arsenide/Antimonide Heterojunction Tunnel FETs With Enhanced Drive Current. <i>IEEE Electron Device Letters</i> , <b>2012</b> , 33, 1568-1570	4.4	74
45	Role of InAs and GaAs terminated heterointerfaces at source/channel on the mixed As-Sb staggered gap tunnel field effect transistor structures grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 024306	2.5	25
44	Defect assistant band alignment transition from staggered to broken gap in mixed As/Sb tunnel field effect transistor heterostructure. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 094312	2.5	25
43	Structural properties and band offset determination of p-channel mixed As/Sb type-II staggered gap tunnel field-effect transistor structure. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 112106	3.4	16
42	Design of metamorphic dual-junction InGaP/GaAs solar cell on Si with efficiency greater than 29% using finite element analysis <b>2012</b> ,		1
41	(Invited) Heterogeneously Integrated III-V on Silicon for Future Nanoelectronics. <i>ECS Transactions</i> , <b>2012</b> , 45, 581-594	1	14
40	Demonstration of improved heteroepitaxy, scaled gate stack and reduced interface states enabling heterojunction tunnel FETs with high drive current and high on-off ratio <b>2012</b> ,		43
39	Effect of Postdeposition Annealing Temperatures on Electrical Characteristics of Molecular-Beam-Deposited HfO <sub>2</sub> on n-InAs/InGaAs MetalOxideSemiconductor Capacitors. <i>Applied Physics Express</i> , <b>2012</b> , 5, 021104	2.4	17

38	High quality Ge thin film grown by ultrahigh vacuum chemical vapor deposition on GaAs substrate. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 161905	3.4	26
37	Dislocation reduction in GaN film using Ga-lean GaN buffer layer and migration enhanced epitaxy. <i>Thin Solid Films</i> , <b>2011</b> , 519, 6208-6213	2.2	14
36	(Invited) Si, SiGe, Ge, and III-V Semiconductor Nanomembranes and Nanowires Enabled by SiGe Epitaxy. <i>ECS Transactions</i> , <b>2010</b> , 33, 777-789	1	4
35	The Roles of Threading Dislocations on Electrical Properties of AlGaIn/GaN Heterostructure Grown by MBE. <i>Journal of the Electrochemical Society</i> , <b>2010</b> , 157, H746	3.9	50
34	Fermi level unpinning of GaSb (100) using plasma enhanced atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2010</b> , 97, 143502	3.4	86
33	The influences of surface treatment and gas annealing conditions on the inversion behaviors of the atomic-layer-deposition Al <sub>2</sub> O <sub>3</sub> /n-In <sub>0.53</sub> Ga <sub>0.47</sub> As metal-oxide-semiconductor capacitor. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 042903	3.4	92
32	Study of the inversion behaviors of Al <sub>2</sub> O <sub>3</sub> /In <sub>x</sub> Ga <sub>1-x</sub> As metal-oxide-semiconductor capacitors with different In contents. <i>Solid-State Electronics</i> , <b>2010</b> , 54, 37-41	1.7	17
31	Strain relaxation properties of InAs <sub>y</sub> P <sub>1-y</sub> metamorphic materials grown on InP substrates. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 061643	2.5	41
30	Surface Preparation and Passivation of III-V Substrates for Future Ultra-High Speed, Low Power Logic Applications. <i>Solid State Phenomena</i> , <b>2009</b> , 145-146, 165-167	0.4	
29	Metamorphic In <sub>0.7</sub> Al <sub>0.3</sub> As/In <sub>0.69</sub> Ga <sub>0.31</sub> As thermophotovoltaic devices grown on graded InAs <sub>y</sub> P <sub>1-y</sub> buffers by molecular beam epitaxy. <i>Solid-State Electronics</i> , <b>2009</b> , 53, 102-106	1.7	19
28	Advanced high-K gate dielectric for high-performance short-channel In <sub>0.7</sub> Ga <sub>0.3</sub> As quantum well field effect transistors on silicon substrate for low power logic applications <b>2009</b> ,		49
27	Kinetic control of self-catalyzed indium phosphide nanowires, nanocones, and nanopillars. <i>Nano Letters</i> , <b>2009</b> , 9, 2207-11	11.5	58
26	Self-catalyzed epitaxial growth of vertical indium phosphide nanowires on silicon. <i>Nano Letters</i> , <b>2009</b> , 9, 2223-8	11.5	65
25	Effect of twinning on the photoluminescence and photoelectrochemical properties of indium phosphide nanowires grown on silicon (111). <i>Nano Letters</i> , <b>2008</b> , 8, 4664-9	11.5	67
24	High-performance 40nm gate length InSb p-channel compressively strained quantum well field effect transistors for low-power (VCC=0.5V) logic applications <b>2008</b> ,		47
23	Integrating III-V on Silicon for Future Nanoelectronics <b>2008</b> ,		12
22	Carrier Transport in High-Mobility III-V Quantum-Well Transistors and Performance Impact for High-Speed Low-Power Logic Applications. <i>IEEE Electron Device Letters</i> , <b>2008</b> , 29, 1094-1097	4.4	51
21	Heterogeneous integration of enhancement mode In <sub>0.7</sub> Ga <sub>0.3</sub> As quantum well transistor on silicon substrate using thin (less than 2 nm) composite buffer architecture for high-speed and low-voltage (0.5 V) logic applications <b>2007</b> ,		23

20	Ultrahigh-Speed 0.5 V Supply Voltage $\text{In}_{0.7}\text{Ga}_{0.3}\text{As}$ Quantum-Well Transistors on Silicon Substrate. <i>IEEE Electron Device Letters</i> , <b>2007</b> , 28, 685-687	4.4	70
19	Gate length scaling study of InAlAs/InGaAs/InAsP composite channel HEMTs. <i>Solid-State Electronics</i> , <b>2007</b> , 51, 838-841	1.7	7
18	Carrier compensation and scattering mechanisms in Si-doped $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ layers grown on InP substrates using intermediate $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ step-graded buffers. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 063705	2.5	13
17	Evidence of interface-induced persistent photoconductivity in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{InP}$ double heterostructures grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 032106	3.4	1
16	Photoconductivity decay in metamorphic $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ double heterostructures grown on $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ compositionally step-graded buffers. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 071908	3.4	4
15	Atomic diffusion and band lineups at $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ -on-InP heterointerfaces. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2005</b> , 23, 1832		10
14	Spatial resolution of ballistic electron emission microscopy measured on metal/quantum-well Schottky contacts. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182105	3.4	15
13	Direct measurement of quantum confinement effects at metal to quantum-well nanocontacts. <i>Physical Review Letters</i> , <b>2005</b> , 94, 206803	7.4	24
12	Atomic layer diffusion and electronic structure at $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{InP}$ interfaces. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>2004</b> , 22, 554		13
11	Comparison of mixed anion, $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ and mixed cation, $\text{In}_x\text{Al}_{1-x}\text{As}$ metamorphic buffers grown by molecular beam epitaxy on (100) InP substrates. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 3952-3960	2.5	47
10	High-quality $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ step-graded buffer by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3212-3214	3.4	29
9	Single-junction InGaP/GaAs solar cells grown on Si substrates with SiGe buffer layers. <i>Progress in Photovoltaics: Research and Applications</i> , <b>2002</b> , 10, 417-426	6.8	100
8	Relaxed InAsP layers grown on step graded InAsP buffers by solid source MBE. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 722, 1021		4
7	Electrical transport characteristics of Au/n-GaAs Schottky diodes on n-Ge at low temperatures. <i>Solid-State Electronics</i> , <b>2001</b> , 45, 133-141	1.7	142
6	Doping dependence of the barrier height and ideality factor of Au/n-GaAs Schottky diodes at low temperatures. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 307, 125-137	2.8	102
5	Interface states density distribution in Au/n-GaAs Schottky diodes on n-Ge and n-GaAs substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 87, 141-147	3.1	84
4	Self-annihilation of antiphase boundaries in GaAs epilayers on Ge substrates grown by metal-organic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 5972-5979	2.5	36
3	Effects of thin oxide in metal/semiconductor and metal/insulator/semiconductor epi-GaAs Schottky diodes. <i>Solid-State Electronics</i> , <b>2000</b> , 44, 1089-1097	1.7	131

- 2 Anomalous current transport in Au/low-doped n-GaAs Schottky barrier diodes at low temperatures. *Applied Physics A: Materials Science and Processing*, **1999**, 68, 49-55 2.6 67
- 1 Photoluminescence studies on Si-doped GaAs/Ge. *Journal of Applied Physics*, **1998**, 83, 4454-4461 2.5 23